REMARKS

In accordance with the foregoing, claims 2, 6, 8, 11, and 15 have been rewritten to independent form, each to incorporate the limitations of claim 1 from which each depends, and claim 1 has been canceled.

Further, various of the dependent claims have been amended for consistency with the independent claims and to improve form.

No new matter is presented.

Approval and entry of the foregoing amended claims are respectfully requested.

ITEM 3: REJECTION OF CLAIMS 1-23 FOR ANTICIPATION UNDER 35 USC § 102(e) BY HISHASHI JP: 09168830

In support of the rejection, the Examiner broadly asserts:

> In paragraphs 11 and 12 of the electronic translation Hishashi teaches a memory controller (fig. 1, section 2), an access request (paragraph 11), a determining circuit (fig. 1, element 4), memory addresses (paragraph 11), wherein the access request will be compared with memory addresses and the auto precharge will be set as enable or disable.

It is respectfully submitted that the mere recitation of structural elements of the Hishashi disclosed structure fails to explain or establish that each limitation of each of the independent claims hereof reads on the reference. This is true, not only for the "control device" (apparatus) independent claims 2, 6, 8, 11, and 15, but even more so for the method independent claims 16, 22, and 23--i.e., the rejection does not even suggest that the Hishashi structural elements perform the recited functions of the independent claims, much less those functions set forth in the latter, independent method claims.

It follows, as well, that the rejection fails to establish anticipation of the inventions as defined by the respective dependent claims which not only inherit the distinguishing limitations of their respective independent claims but, as well, set forth their own, respective and different, patentably distinguishing method recitations.

THE HISHASHI REFERENCE

Hishashi (Japanese Application No. 09168830) discloses a memory command control circuit, in which either a read/write command with auto precharge or a read/write command is selectively issued to SDRAM.

The memory command control circuit of Hishashi is for comparing addresses of a precedent memory request and a consecutive memory request, and determining whether the auto precharge is set as enable or disable in accordance with the comparison result. That is, in Hishashi, it is determined whether a memory request, of the same line address access, is issued or not by comparing addresses of a precedent memory request and a consecutive memory request-- and, based on the result, a command with auto precharge or a normal command is issued.

On the other hand, in the present invention, it is determined, using only one access request, whether an auto precharge function is enabled or not, and an access instruction is supplied to a semiconductor memory.

Namely, in the present invention, it is judged from only one access request whether the auto precharge function is enabled or not. Accordingly, the present invention has different compositions and effects from Hishashi, in which plural access requests to a memory are received and it is determined from the plural access requests whether the auto precharge is to be enabled or not. Hishashi fails to disclose that, as in the present invention, it is judged from only one access request whether the auto precharge function is enabled, or not.

CONCLUSION

Accordingly, it is respectfully submitted that the pending claims patentably distinguish over the reference. Further, there being no other objections or rejections, it is submitted that the application is in condition for allowance, which action is earnestly solicited.

If there are any additional fees associated with filing of this Amendment, please charge the same to our Deposit Account No. 19-3935.

Respectfully submitted,

STAAS & HALSEY LLP

Date: April 15, 2004

By: _____
H. J. Staas
Registration No. 22,010

1201 New York Avenue, NW, Suite 700
Washington, D.C. 20005
Telephone: (202) 434-1500
Facsimile: (202) 434-1501

CERTIFICATE UNDER 37 CFR 1.8(a)
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450
on _____, 20__
STAAS & HALSEY
By: _____
Date: _____